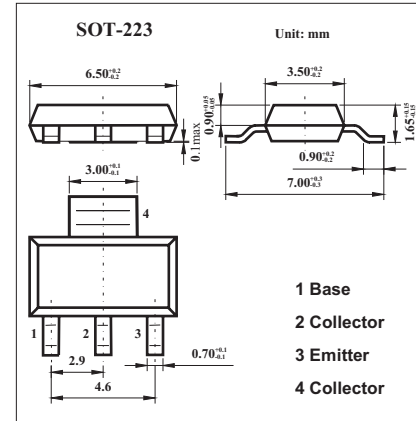


PNP Silicon Planar High Voltage Transistor

FZTA92

■ Features

- High breakdown voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Base Current	I _B	-100	mA
Continuous Collector Current	I _C	-500	mA
Power Dissipation at Tamb=25°C	P _{tot}	2	W
Operating and Storage Temperature Range	T _J :T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-300			V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0*	-300			V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-200V, I _E =0			-0.25	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-3V, I _C =0			-0.1	μA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-20mA, I _B =-2mA			-0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-20mA, I _B =-2mA			-0.9	V
Static Forward Current Transfer Ratio	h _{FE}	I _C =-1mA, V _{CE} =-10V*	25			
		I _C =-10mA, V _{CE} =-10V*	40			
		I _C =-30mA, V _{CE} =-10V*	25			
Transition Frequency	f _T	I _C =-10mA, V _{CE} =-20V, f=20MHz	50			MHz
Output Capacitance	C _{obo}	V _{CB} =-20V, f=1MHz			6	pF

* Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%